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# **Joint Symposium: State-of-the-Art Program on Compound Semiconductors 63 (SOTAPOCS 63) -and- GaN and SiC Power Technologies 10**

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**Table of Contents**

<i>Preface</i>	<i>iii</i>
<b>Chapter 2</b>	
<b>H01 – Ultrawide Bandgap Materials and Devices</b>	
<i>(Invited) Insights into the UV-C Optical Absorption of AlN Substrates Grown by PVT</i> <i>R. Dalmau, J. Britt, R. Schlessler</i>	3
<b>Chapter 3</b>	
<b>H01 – Bulk GaN Growth and Characterization</b>	
The Structural Evolution of Dot-Core GaN Substrates with Annealing Under Growth-Like Conditions <i>M. E. Liao, K. Huynh, Y. Wang, A. A. Allerman, M. S. Goorsky</i>	15
Synchrotron X-ray Topography Characterization of Commercial GaN Substrates for Power Electronic Applications <i>Y. Liu, S. Hu, H. Peng, T. Ailihumaer, B. Raghathamachar, M. Dudley</i>	21
<b>Chapter 4</b>	
<b>H01 – GaN Devices</b>	
<i>(Invited) Ruggedness of SiC and GaN Power Transistors in Switching Based Tests</i> <i>R. Zhang, J. Kozak, J. Liu, Y. Zhang</i>	37
Design of Ion-Implanted Junction Termination Extension for Vertical GaN Pin Rectifiers <i>M. Cho, Z. Xu, M. Bakhtiary-Noodeh, T. Detchphrom, R. D. Dupuis, S. C. Shen</i>	49

**Chapter 5**  
**H01 – GaN Epitaxy**

*(Invited)* GaN Homoepitaxial Growth and Substrate-Dependent Effects for Vertical Power Devices 63  
*J. K. Hite, M. A. Mastro, T. J. Anderson, J. C. Gallagher, M. Ebrish, J. A. Freitas Jr.*

*(Invited)* A Path Toward Vertical GaN Superjunction Devices 69  
*D. Khachariya, D. Szymanski, P. Reddy, E. Kohn, Z. Sitar, R. Collazo, S. Pavlidis*

**Chapter 6**  
**H01 – Modeling of Compound Semiconductor Materials**

III-Nitride Based Narrow Band Far-UVC LEDs for Airborne and Surface Disinfection 83  
*H. Q. T. Bui, R. T. Velpula, B. Jain, H. P. T. Nguyen*

**Chapter 7**  
**H01 – Packaging and Heterogeneous Integration**

*(Invited)* Heterogeneous Integration of Silicon CMOS Electronics and Compound Semiconductor Electronics for Miniature RF Photonic Transceivers 93  
*C. D. Nordquist, E. Skogen, S. Fortuna, A. E. Hollowell, C. Hemmady, J. Saugen, T. Forbes, M. G. Wood, M. Jordan, J. McClain, S. Lepkowski, C. Alford, G. Peake, A. Pomerene, C. M. Long, D. Serkland, K. A. Dean*

**Chapter 8**  
**H01 – GaAs, 2D Materials, and Other Compound Semiconductors**

Characterization of Hazy Morphology on AlInP/GaAs Epitaxial Wafers Grown by Organometallic Vapor Phase Epitaxy 109  
*H. Peng, T. Ailihumaer, Y. Liu, B. Raghathamachar, M. Dudley*

**Chapter 9**  
**H01 – SiC Materials and Devices**

(Invited) P-Type and N-Type Channeling Ion Implantation of SiC and Implications for Device Design and Fabrication <i>H. Das, S. Sunkari, J. Justice, R. Malousek, J. Chochol, R. Wada, T. Kuroi</i>	119
Characterization of Dislocations in 4H-SiC Single Crystals at the Initial Growth Stage by Synchrotron X-ray Topography <i>T. Ailihumaer, H. Peng, Y. Liu, B. Raghathamachar, M. Dudley</i>	125
Analysis of Dislocations in PVT-Grown 6H-SiC through Grazing-Incidence X-Ray Topographic Images and Ray-Tracing Simulation <i>Q. Cheng, T. Ailihumaer, H. Peng, Y. Liu, B. Raghathamachar, M. Dudley</i>	133

## **Chapter 10**

### **H01 – Poster Session**

Selective-Area Growth of AlInAs Nanowires <i>Y. Tai, H. Gamo, J. Motohisa, K. Tomioka</i>	149
A Simple Approach to Growth Mode of InN and InGaN Thin Films on GaN(0001) Substrate <i>K. Nagai, T. Akiyama, K. Nakamura, T. Ito</i>	155
Author Index	165